

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	17	system and process\$3 near chamber and seed near layer and x-ray	USPAT; EPO; JPO; DERWEN T	2003/03/11 16:21
2	BRS	L2	4	semiconductor near process\$3 near system and chamber and x-ray and measurement	USPAT; EPO; JPO; DERWEN T	2003/03/11 17:32
3	BRS	L3	113	singh near bhanwar	USPAT; EPO; JPO; DERWEN T	2003/03/11 17:47
4	BRS	L4	316	system and substrate and chamber and trench and measurement	USPAT; EPO; JPO; DERWEN T	2003/03/11 18:05
5	BRS	L5	425580 1	system and x-ray and chamber and trench and measurement	USPAT; EPO; JPO; DERWEN T	2003/03/11 18:06
6	BRS	L6	68	system and x-ray and chamber and trench and measurement	USPAT; EPO; JPO; DERWEN T	2003/03/11 18:13
7	BRS	L7	14	scatter\$3 near measurement and process\$3 near chamber	USPAT; EPO; JPO; DERWEN T	2003/03/11 18:23

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	17	system and process\$3 near chamber and seed near layer and x-ray	USPAT; EPO; JPO; DERWEN T	2003/03/11 16:21